

ABSTRACT

The 1N306 is a highly popular glass passivated germanium diode that features a low leakage current, flat junction capacitance, and high mechanical strength. This device is recommended for applications such as AM/FM detectors, ratio detectors, FM discriminators, TV audio detectors, RF input probes, and TV video detectors.

The 1N306 can also be used in many more AM, FM, and TV-IF applications, replacing point contact devices.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min.	Max.	Units
Peak Inverse Voltage (Repetitive), Measured @ I_R = 1mA	PIV		15	Volts
Peak Forward Surge Current Non-Repetitive, t=1s	IFSM		0.5	Amps
Peak Forward Surge Current Repetitive	IFSR		100	mA
Average Rectified Forward Current	lo			mA
Operating and Storage Temperature Range	TJ/TSTG	-55	+75	°C
T _{amb} = 25°C				

ELECTRICAL CHARACTERISTICS

Parameter	Test Conditions	Symbol	Min.	Max.	Units
Forward Voltage Drop	I _F = 5.0mA	VF		1.0	Volts
Reverse Leakage	V _R = 10 Volts	IR		2	μΑ
	V _R = 50 Volts	I _R			μA
Breakdown Voltage	I _R = 1.0 mA	PIV	65		Volts

T_{amb} = 25°C

MECHANICAL DIMENSIONS



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